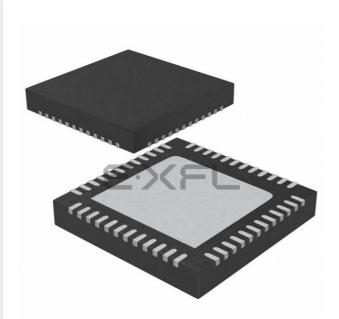
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Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, LINbus, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	36
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K × 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D - 16bit; D/A - 12bit
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	48-QFN (7x7)
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Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV = 01)	2.48	2.56	2.64	V	_
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV = 00)	2.62	2.70	2.78	v	
V_{LVW2H}	 Level 2 falling (LVWV = 01) 	2.72	2.80	2.88	v	
V _{LVW3H}	 Level 3 falling (LVWV = 10) 	2.82	2.90	2.98	v	
$V_{\rm LVW4H}$	• Level 4 falling (LVWV = 11)	2.92	3.00	3.08	v	
V _{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	_	±60	_	mV	_
V _{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	-
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV = 00)	1.74	1.80	1.86	v	
V_{LVW2L}	 Level 2 falling (LVWV = 01) 	1.84	1.90	1.96	v	
V_{LVW3L}	 Level 3 falling (LVWV = 10) 	1.94	2.00	2.06	v	
V_{LVW4L}	• Level 4 falling (LVWV = 11)	2.04	2.10	2.16	v	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	-	mV	-
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	-
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	-

Table 6	V _{DD} supply LVD and POR	operating require	ments (continued)
	VDD Supply LVD and I On V	operating require	mente (continueu)

1. Rising thresholds are falling threshold + hysteresis voltage

2.2.3 Voltage and current operating behaviors Table 7. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — Normal drive pad (except RESET_b)				1, 2
		V _{DD} – 0.5	—	V	
	• $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 3.6 \text{ V}, \text{ I}_{\text{OH}} = -5 \text{ mA}$	V _{DD} – 0.5	—	V	
	• $1.71 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}, \text{ I}_{\text{OH}} = -2.5 \text{ mA}$				
V _{OH}	Output high voltage — High drive pad (except				1, 2
	RESET_b)	V _{DD} – 0.5	—	V	
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OH} = -20 mA	V _{DD} – 0.5	_	v	
	• 1.71 V \leq V _{DD} \leq 2.7 V, I _{OH} = -10 mA				
I _{ОНТ}	Output high current total for all ports	-	100	mA	

Table continues on the next page...





Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	 VLLS0 → RUN 					
		—	106	120	μs	
	 VLLS1 → RUN 					
		—	105	117	μs	
	 VLLS3 → RUN 					
		—	47	54	μs	
	• LLS → RUN					
		—	4.5	5.0	μs	
	 VLPS → RUN 					
		—	4.5	5.0	μs	
	• STOP → RUN					
			4.5	5.0	μs	

 Table 8. Power mode transition operating behaviors (continued)

1. Normal boot (FTFA_FOPT[LPBOOT]=11).

2.2.5 Power consumption operating behaviors

The maximum values stated in the following table represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

Symbol	Description	Temp.	Тур.	Max	Unit	Note
I _{DDA}	Analog supply current	—	_	See note	mA	1
IDD_RUNCO_CM	Run mode current in compute operation - 48 MHz core / 24 MHz flash/ bus disabled, LPTMR running using 4 MHz internal reference clock, CoreMark® benchmark code executing from flash, at 3.0 V	_	6.1	_	mA	2
I _{DD_RUNCO}	Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus clock disabled, code of while(1) loop executing from flash, at 3.0 V	-	3.8	4.4	mA	3
I _{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks disabled, code executing from flash, at 3.0 V	_	4.6	5.2	mA	3

Table 9. Power consumption operating behaviors

Table continues on the next page...

9



Symbol	Description	Temp.	Тур.	Max	Unit	Note
		at 85 °C	21.13	39.13	μA	
		at 105 °C	45.85	85.45	μA	
I _{DD_LLS}	Low leakage stop mode current at 3.0	at 25 °C	1.98	2.65	μA	—
	V	at 50 °C	3.13	4.35	μA	
		at 70 °C	5.65	8.34	μA	
		at 85 °C	9.58	14.29	μA	-
		at 105 °C	20.52	31.74	μA	
I _{DD_VLLS3}	Very low-leakage stop mode 3 current	at 25 °C	1.46	2.06	μA	—
	at 3.0 V	at 50 °C	2.29	3.22	μA	-
		at 70 °C	4.10	5.90	μA	
		at 85 °C	6.93	10.02	μA	
		at 105 °C	14.80	22.12	μA	-
I _{DD_VLLS1}	Very low-leakage stop mode 1 current	at 25 °C	0.71	1.20	μA	—
	at 3.0V	at 50 °C	1.10	1.71	μA	-
		at 70 °C	2.09	3.03	μA	-
		at 85 °C	3.80	5.42	μA	-
		at 105 °C	8.84	12.98	μA	
IDD_VLLS0	Very low-leakage stop mode 0 current	at 25 °C	0.40	0.88	μA	_
	(SMC_STOPCTRL[PORPO] = 0) at 3.0 V	at 50 °C	0.80	1.40	μA	-
	5.0 V	at 70 °C	1.79	2.72	μA	
		at 85 °C	3.50	5.10	μA	
		at 105 °C	8.54	12.63	μA	
IDD_VLLS0	Very low-leakage stop mode 0 current	at 25 °C	0.23	0.69	μA	7
	(SMC_STOPCTRL[PORPO] = 1) at 3.0 V	at 50 °C	0.61	1.19	μA	1
	0.0 V	at 70 °C	1.59	2.50	μA	1
		at 85 °C	3.30	4.89	μA	
		at 105 °C	8.36	12.41	μA	1

Table 9. Power consumption operating behaviors (continued)

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.

2. MCG configured for PEE mode. CoreMark benchmark compiled using IAR 6.40 with optimization level high, optimized for balanced.

- 3. MCG configured for FEI mode.
- 4. Incremental current consumption from peripheral activity is not included.
- 5. MCG configured for BLPI mode. CoreMark benchmark compiled using IAR 6.40 with optimization level high, optimized for balanced.
- 6. MCG configured for BLPI mode.
- 7. No brownout.



Symbol	Description			٦	empera	ature (°	C)		Unit
			-40	25	50	70	85	105	
I _{IREFSTEN4MHz}	4 MHz internal reference clock Measured by entering STOP o with 4 MHz IRC enabled.		56	56	56	56	56	56	μA
I _{IREFSTEN32KHz}				52	52	52	52	52	μA
I _{EREFSTEN4MHz}		External 4 MHz crystal clock adder. Measured by entering STOP or VLPS mode with the crystal enabled.		228	237	245	251	258	μA
I _{EREFSTEN32KHz}			440	490	540	560	570	580	nA
	adder by means of the VLLS OSC0_CR[EREFSTEN and EREFSTEN] bits. Measured LLS		440	490	540	560	570	580	
			490	490	540	560	570	680	
	by entering all modes with the	VLPS	510	560	560	560	610	680	
	crystal enabled.	STOP	510	560	560	560	610	680	
I _{CMP}	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.			22	22	22	22	22	μA
I _{RTC}	RTC peripheral adder measure the device in VLLS1 mode with kHz crystal enabled by means RTC_CR[OSCE] bit and the R for 1 minute. Includes ERCLK3 external crystal) power consum	of the TC ALARM set 32K (32 kHz	432	357	388	475	532	810	nA
I _{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at	MCGIRCLK (4 MHz internal reference clock)	66	66	66	66	66	66	μA
	115200 baud rate. Includes selected clock source power consumption.	115200 baud rate. Includes selected clock source power (4 MHz		237	246	254	260	268	
I _{TPM}	TPM peripheral adderMCGIRCLKmeasured by placing the(4 MHzdevice in STOP or VLPSinternalmode with selected clockreferencesource configured for outputclock)		86	86	86	86	86	86	μA
	compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents.	OSCERCLK (4 MHz external crystal)	235	256	265	274	280	287	

Table 10. Low power mode peripheral adders — typical value

Table continues on the next page...



Symbol	bol Description Temperature (°C)						Unit	
		-40	25	50	70	85	105	
I _{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	μA
IADC	ADC peripheral adder combining the measured values at V_{DD} and V_{DDA} by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	366	366	366	366	366	366	μA

 Table 10.
 Low power mode peripheral adders — typical value (continued)

2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE for run mode, and BLPE for VLPR mode
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA



application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

- 2. $V_{DD} = 3.3 \text{ V}$, $T_A = 25 \text{ °C}$, $f_{OSC} = 8 \text{ MHz}$ (crystal), $f_{SYS} = 48 \text{ MHz}$, $f_{BUS} = 24 \text{ MHz}$
- 3. Specified according to Annex D of IEC Standard 61967-2, Measurement of Radiated Emissions TEM Cell and Wideband TEM Cell Method

2.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

- 1. Go to www.freescale.com.
- 2. Perform a keyword search for "EMC design."

2.2.8 Capacitance attributes

Table 12. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C _{IN}	Input capacitance	—	7	pF

2.3 Switching specifications

2.3.1 Device clock specifications

Table 13. Device clock specifications

Symbol	Description	Min.	Max.	Unit
	Normal run mode	•		
f _{SYS}	System and core clock	_	48	MHz
f _{BUS}	Bus clock	_	24	MHz
f _{FLASH}	Flash clock	—	24	MHz
f _{SYS_USB}	System and core clock when Full Speed USB in operation	20	_	MHz
f _{LPTMR}	LPTMR clock	—	24	MHz
	VLPR and VLPS modes ¹			
f _{SYS}	System and core clock	—	4	MHz
f _{BUS}	Bus clock	_	1	MHz
f _{FLASH}	Flash clock	-	1	MHz
f _{LPTMR}	LPTMR clock ²	—	24	MHz

Table continues on the next page...



2.4.2 Thermal attributes Table 16. Thermal attributes

Board type	Symbol	Description	64 LQFP	48 QFN	32 QFN	Unit	Notes
Single-layer (1S)	R _{θJA}	Thermal resistance, junction to ambient (natural convection)	71	83	98	°C/W	1
Four-layer (2s2p)	R _{θJA}	Thermal resistance, junction to ambient (natural convection)	53	30	34	°C/W	
Single-layer (1S)	R _{θJMA}	Thermal resistance, junction to ambient (200 ft./min. air speed)	59	68	82	°C/W	
Four-layer (2s2p)	R _{θJMA}	Thermal resistance, junction to ambient (200 ft./min. air speed)	46	24	28	°C/W	
_	R _{θJB}	Thermal resistance, junction to board	35	12	13	°C/W	2
_	R _{θJC}	Thermal resistance, junction to case	21	2.3	2.3	°C/W	3
_	Ψ _{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	6	5	8	°C/W	4

- 1. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air), or EIA/JEDEC Standard JESD51-6, Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air).
- 2. Determined according to JEDEC Standard JESD51-8, Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board.
- 3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
- 4. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air).

3 Peripheral operating requirements and behaviors

3.1 Core modules



3.1.1 SWD electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation			
	Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	_	ns
JЗ	SWD_CLK clock pulse width			
	Serial wire debug	20	_	ns
J4	SWD_CLK rise and fall times	_	3	ns
J 9	SWD_DIO input data setup time to SWD_CLK rise	10	_	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	—	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	_	ns

Table 17. SWD full voltage range electricals

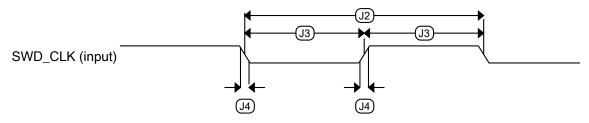


Figure 4. Serial wire clock input timing



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	• 24 MHz		1.5		mA	
	• 32 MHz					
I _{DDOSC}	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	_	μA	
	• 4 MHz	—	400	_	μA	
	• 8 MHz (RANGE=01)	—	500	_	μA	
	• 16 MHz	—	2.5	_	mA	
	• 24 MHz	—	3	_	mA	
	• 32 MHz	—	4	_	mA	
C _x	EXTAL load capacitance					2, 3
Cy	XTAL load capacitance	_	—	—		2, 3
R _F	Feedback resistor — low-frequency, low-power mode (HGO=0)	_			MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	_	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	_			MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	_	1	_	MΩ	
R _S	Series resistor — low-frequency, low-power mode (HGO=0)	—	_	_	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	_	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	_	_	_	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)					
		_	0	_	kΩ	
V _{pp} ⁵	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	_	0.6	_	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	_	V _{DD}	_	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	_	0.6	_	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	_	V _{DD}	_	V	

Table 19. Oscillator DC electrical specifications (continued)

V_{DD}=3.3 V, Temperature =25 °C
 See crystal or resonator manufacturer's recommendation



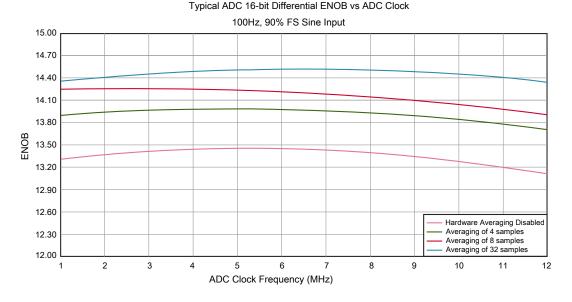
		a					
Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
INL	Integral non- linearity	12-bit modes	_	±1.0	–2.7 to +1.9	LSB ⁴	5
		 <12-bit modes 	_	±0.5	–0.7 to +0.5		
E _{FS}	Full-scale error	12-bit modes	_	-4	-5.4	LSB ⁴	V _{ADIN} =
		<12-bit modes	_	-1.4	-1.8		V _{DDA} ⁵
EQ	Quantization	16-bit modes	_	-1 to 0	—	LSB ⁴	
	error	• ≤13-bit modes	—	-	±0.5		
ENOB	Effective number	16-bit differential mode	12.8	14.5		bits	6
	of bits	• Avg = 32	11.9	13.8	_	bits	
		• Avg = 4					
		10 bit single and shows de	12.2	13.9	_	bits	
		16-bit single-ended mode	11.4	13.1	_	bits	
		• Avg = 32					
		• Avg = 4					
SINAD	Signal-to-noise plus distortion	See ENOB	6.02	2 × ENOB +	1.76	dB	
THD	Total harmonic	16-bit differential mode	_	-94	_	dB	7
	distortion	• Avg = 32					
			_	-85	_	dB	
		16-bit single-ended mode					
		• Avg = 32					
SFDR	Spurious free	16-bit differential mode	82	95	_	dB	7
	dynamic range	• Avg = 32	70				
		16 bit single anded made	78	90	_	dB	
		16-bit single-ended mode					
		• Avg = 32					
EIL	Input leakage error			$I_{In} \times R_{AS}$		mV	I _{In} = leakage current
							(refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	8
V _{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

Table 26. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

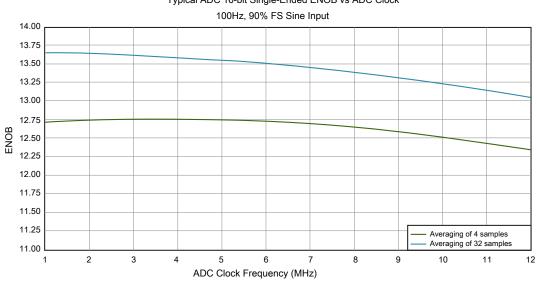


Peripheral operating requirements and behaviors

- 1. All accuracy numbers assume the ADC is calibrated with V_{REFH} = V_{DDA}
- 2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
- 3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
- 4. 1 LSB = $(V_{\text{REFH}} V_{\text{REFL}})/2^{N}$
- 5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
- 6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
- 7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
- 8. ADC conversion clock < 3 MHz







Typical ADC 16-bit Single-Ended ENOB vs ADC Clock





NOTE

The MCGPLLCLK meets the USB jitter specifications for certification with the use of an external clock/crystal for both Device and Host modes.

The MCGFLLCLK does not meet the USB jitter specifications for certification.

3.8.2 USB VREG electrical specifications Table 30. USB VREG electrical specifications

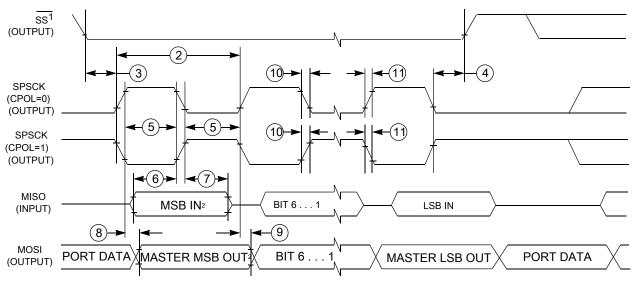
Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
VREGIN	Input supply voltage	2.7	—	5.5	V	
I _{DDon}	Quiescent current — Run mode, load current equal zero, input supply (VREGIN) > 3.6 V	_	125	186	μA	
I _{DDstby}	Quiescent current — Standby mode, load current equal zero	_	1.1	10	μA	
I _{DDoff}	 Quiescent current — Shutdown mode VREGIN = 5.0 V and temperature=25 °C Across operating voltage and temperature 	_	650 —	4	nA μA	
I _{LOADrun}	Maximum load current — Run mode			120	mA	
I _{LOADstby} V _{Reg33out}	Maximum load current — Standby mode Regulator output voltage — Input supply (VREGIN) > 3.6 V			1	mA	
	Run modeStandby mode	3 2.1	3.3 2.8	3.6 3.6	V V	
V _{Reg33out}	Regulator output voltage — Input supply (VREGIN) < 3.6 V, pass-through mode	2.1	_	3.6	V	2
C _{OUT}	External output capacitor	1.76	2.2	8.16	μF	
ESR	External output capacitor equivalent series resistance	1	—	100	mΩ	
I _{LIM}	Short circuit current	_	290	_	mA	

1. Typical values assume VREGIN = 5.0 V, Temp = 25 $^\circ\text{C}$ unless otherwise stated.

2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to ILoad.



Peripheral operating requirements and behaviors



1.If configured as output

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 14. SPI master mode timing (CPHA = 1)

Table 33.	SPI slave mode timing on slew rate disabled pads
-----------	--

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f _{op}	Frequency of operation	0	f _{periph} /4	Hz	1
2	t _{SPSCK}	SPSCK period	4 x t _{periph}	—	ns	2
3	t _{Lead}	Enable lead time	1	—	t _{periph}	—
4	t _{Lag}	Enable lag time	1	—	t _{periph}	—
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{periph} - 30	—	ns	—
6	t _{SU}	Data setup time (inputs)	2.5	_	ns	—
7	t _{HI}	Data hold time (inputs)	3.5	_	ns	—
8	t _a	Slave access time	_	t _{periph}	ns	3
9	t _{dis}	Slave MISO disable time	—	t _{periph}	ns	4
10	t _v	Data valid (after SPSCK edge)	—	31	ns	—
11	t _{HO}	Data hold time (outputs)	0	_	ns	—
12	t _{RI}	Rise time input	_	t _{periph} - 25	ns	—
	t _{FI}	Fall time input]			
13	t _{RO}	Rise time output	—	25	ns	_
	t _{FO}	Fall time output]			

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).

- 2. $t_{periph} = 1/f_{periph}$
- 3. Time to data active from high-impedance state
- 4. Hold time to high-impedance state

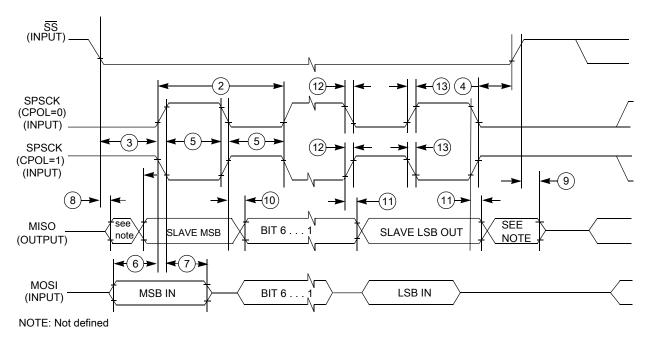


Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f _{op}	Frequency of operation	0	f _{periph} /4	Hz	1
2	t _{SPSCK}	SPSCK period	4 x t _{periph}		ns	2
3	t _{Lead}	Enable lead time	1	—	t _{periph}	_
4	t _{Lag}	Enable lag time	1	—	t _{periph}	—
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{periph} - 30	_	ns	—
6	t _{SU}	Data setup time (inputs)	2	—	ns	_
7	t _{HI}	Data hold time (inputs)	7	_	ns	_
8	t _a	Slave access time	—	t _{periph}	ns	3
9	t _{dis}	Slave MISO disable time	—	t _{periph}	ns	4
10	t _v	Data valid (after SPSCK edge)	—	122	ns	_
11	t _{HO}	Data hold time (outputs)	0	_	ns	—
12	t _{RI}	Rise time input	—	t _{periph} - 25	ns	—
	t _{FI}	Fall time input				
13	t _{RO}	Rise time output	—	36	ns	_
	t _{FO}	Fall time output				

Table 34. SPI slave mode timing on slew rate enabled pads

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).

- 2. $t_{periph} = 1/f_{periph}$
- 3. Time to data active from high-impedance state
- 4. Hold time to high-impedance state



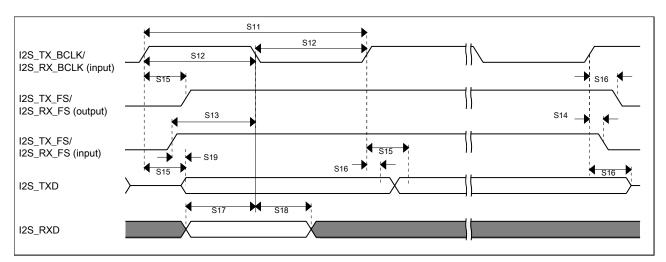




Num.	Characteristic	Min.	Max.	Unit
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	-	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK		-	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	_		ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK		_	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid ¹	—	72	ns

Table 39. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)(continued)

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear





3.9 Human-machine interfaces (HMI)

3.9.1 TSI electrical specifications

Table 40. TSI electrical specifications

Sy	ymbol	Description	Min.	Тур.	Max.	Unit
TSI_	_RUNF	Fixed power consumption in run mode	_	100		μA

Table continues on the next page ...

64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
1	_	1	PTE0	DISABLED		PTE0	SPI1_MISO	UART1_TX	RTC_ CLKOUT	CMP0_OUT	I2C1_SDA	
2	_	-	PTE1	DISABLED		PTE1	SPI1_MOSI	UART1_RX		SPI1_MISO	I2C1_SCL	
3	1	_	VDD	VDD	VDD		_	_		_	_	
4	2	2	VSS	VSS	VSS							
5	3	3	USB0_DP	USB0_DP	USB0_DP							
6	4	4	USB0_DM	USB0_DM	USB0_DM							
7	5	5	VOUT33	VOUT33	VOUT33							
8	6	6	VREGIN	VREGIN	VREGIN							
9	7	-	PTE20	ADC0_DP0/ ADC0_SE0	ADC0_DP0/ ADC0_SE0	PTE20		TPM1_CH0	UART0_TX			
10	8	_	PTE21	ADC0_DM0/ ADC0_SE4a	ADC0_DM0/ ADC0_SE4a	PTE21		TPM1_CH1	UART0_RX			
11	_	_	PTE22	ADC0_DP3/ ADC0_SE3	ADC0_DP3/ ADC0_SE3	PTE22		TPM2_CH0	UART2_TX			
12	_	_	PTE23	ADC0_DM3/ ADC0_SE7a	ADC0_DM3/ ADC0_SE7a	PTE23		TPM2_CH1	UART2_RX			
13	9	7	VDDA	VDDA	VDDA							
14	10	_	VREFH	VREFH	VREFH							
15	11	-	VREFL	VREFL	VREFL							
16	12	8	VSSA	VSSA	VSSA							
17	13	-	PTE29	CMP0_IN5/ ADC0_SE4b	CMP0_IN5/ ADC0_SE4b	PTE29		TPM0_CH2	TPM_CLKIN0			
18	14	9	PTE30	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	DAC0_OUT/ ADC0_SE23/ CMP0_IN4	PTE30		TPM0_CH3	TPM_CLKIN1			
19	_	_	PTE31	DISABLED		PTE31		TPM0_CH4				
20	15	-	PTE24	DISABLED		PTE24		TPM0_CH0		I2C0_SCL		
21	16	_	PTE25	DISABLED		PTE25		TPM0_CH1		I2C0_SDA		
22	17	10	PTA0	SWD_CLK	TSI0_CH1	PTA0		TPM0_CH5				SWD_CLK
23	18	11	PTA1	DISABLED	TSI0_CH2	PTA1	UART0_RX	TPM2_CH0				
24	19	12	PTA2	DISABLED	TSI0_CH3	PTA2	UART0_TX	TPM2_CH1				
25	20	13	PTA3	SWD_DIO	TSI0_CH4	PTA3	I2C1_SCL	TPM0_CH0				SWD_DIO
26	21	14	PTA4	NMI_b	TSI0_CH5	PTA4	I2C1_SDA	TPM0_CH1				NMI_b
27	-	-	PTA5	DISABLED		PTA5	USB_CLKIN	TPM0_CH2			I2S0_TX_ BCLK	
28	-	_	PTA12	DISABLED		PTA12		TPM1_CH0			I2S0_TXD0	
29	_	_	PTA13	DISABLED		PTA13		TPM1_CH1			I2S0_TX_FS	
30	22	15	VDD	VDD	VDD							
31	23	16	VSS	VSS	VSS							
32	24	17	PTA18	EXTAL0	EXTAL0	PTA18		UART1_RX	TPM_CLKIN0			
33	25	18	PTA19	XTAL0	XTAL0	PTA19		UART1_TX	TPM_CLKIN1		LPTMR0_ ALT1	

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7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

7.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	 M = Fully qualified, general market flow P = Prequalification
KL##	Kinetis family	• KL26
A	Key attribute	• Z = Cortex-M0+
FFF	Program flash memory size	 32 = 32 KB 64 = 64 KB 128 = 128 KB
R	Silicon revision	 (Blank) = Main A = Revision after main
Т	Temperature range (°C)	• V = -40 to 105
PP	Package identifier	 FM = 32 QFN (5 mm x 5 mm) FT = 48 QFN (7 mm x 7 mm) LH = 64 LQFP (10 mm x 10 mm)
CC	Maximum CPU frequency (MHz)	• 4 = 48 MHz
N	Packaging type	R = Tape and reel

7.4 Example

This is an example part number:

MKL26Z128VFM4



8 Terminology and guidelines

8.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

8.1.1 Example

This is an example of an operating requirement:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	0.9	1.1	V

8.2 Definition: Operating behavior

Unless otherwise specified, an *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

8.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

8.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF



8.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

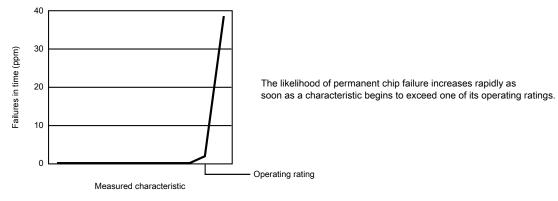
- Operating ratings apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

8.4.1 Example

This is an example of an operating rating:

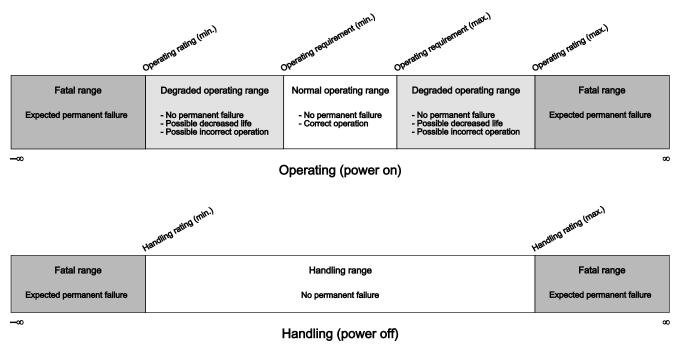
Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	-0.3	1.2	V

8.5 Result of exceeding a rating





8.6 Relationship between ratings and operating requirements



8.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

8.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.